

## Schottky Barrier Rectifiers

Using the Schottky Barrier principle with a Refractory barrier metal. These state-of-the-art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for low voltage, high frequency rectification, or as free wheeling and polarity protection diodes.

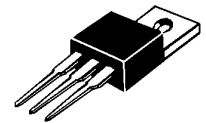
### Features

- \* Low Forward Voltage.
- \* Low Switching noise.
- \* High Current Capacity
- \* Guarantee Reverse Avalanche.
- \* Guard-Ring for Stress Protection.
- \* Low Power Loss & High efficiency.
- \* 150°C Operating Junction Temperature
- \* Low Stored Charge Majority Carrier Conduction.
- \* Plastic Material used Carries Underwriters Laboratory Flammability Classification 94V-O
- \* Pb free
- \* In compliance with EU RoHs directives

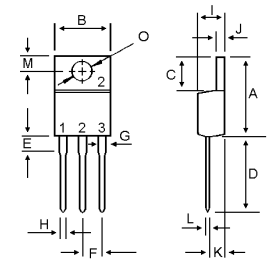


### SCHOTTKY BARRIER RECTIFIERS

**16 AMPERES  
45 VOLTS**



**TO-220AB**



DIM	MILLIMETERS	
	MIN	MAX
A	14.68	16.00
B	9.78	10.42
C	5.02	6.60
D	13.00	14.62
E	3.10	4.19
F	2.41	2.67
G	1.10	1.67
H	0.69	1.01
I	4.22	4.98
J	1.14	1.40
K	2.20	3.30
L	0.28	0.61
M	2.48	3.00
O	3.50	4.00

### MAXIMUM RATINGS

Characteristic	Symbol	S16C45C	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	45	V
RMS Reverse Voltage	$V_{R(RMS)}$	32	V
Average Rectifier Forward Current (per diode) Total Device (Rated $V_R$ )	$I_{F(AV)}$	8 16	A
Peak Repetitive Forward Current (Rate $V_R$ , Square Wave, 20kHz)	$I_{FM}$	16	A
Non-Repetitive Peak Surge Current (Surge applied at rate load conditions half-wave, single phase, 60Hz)	$I_{FSM}$	125	A
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-65 to +150	°C

### ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Maximum Instantaneous Forward Voltage ( $I_F = 8$ Amp $T_C = 25^\circ C$ ) ( $I_F = 8$ Amp $T_C = 125^\circ C$ )	$V_F$	---	0.53 0.48	0.60 ---	V
Maximum Instantaneous Reverse Current (Rated DC Voltage, $T_C = 25^\circ C$ ) (Rated DC Voltage, $T_C = 125^\circ C$ )	$I_R$	---	0.04 30	0.5 ---	mA
Typical Thermal Resistance junction to case	$R_{\theta jc}$		3.8		°C/w

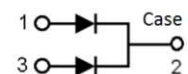


FIG-1 TYPICAL FORWARD CURRENT DERATING CURVE

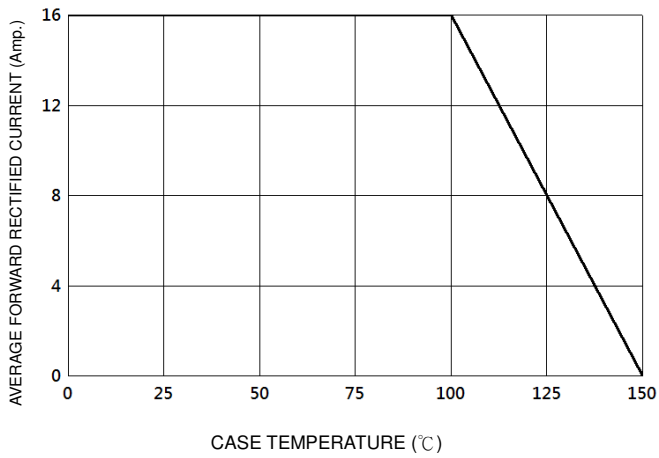


FIG-2 TYPICAL FORWARD CHARACTERISTICS

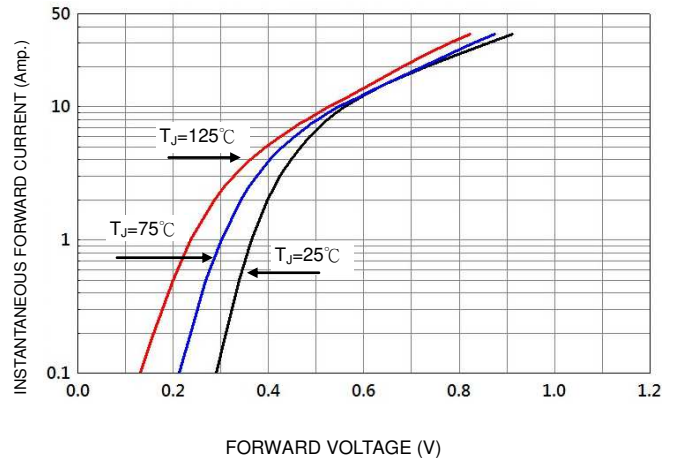


FIG-3 TYPICAL REVERSE CHARACTERISTICS

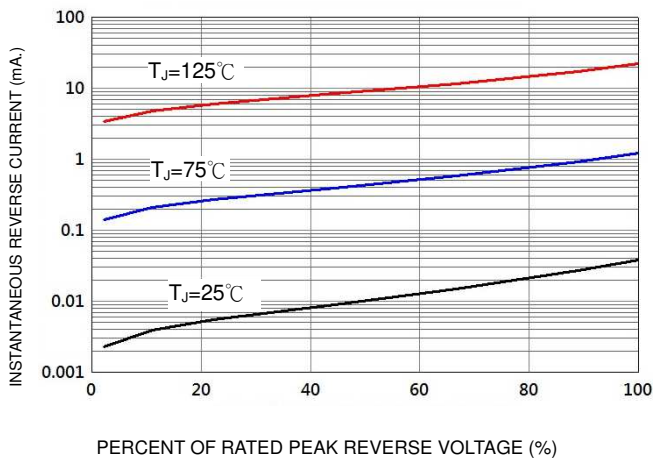


FIG-4 TYPICAL JUNCTION CAPACITANCE

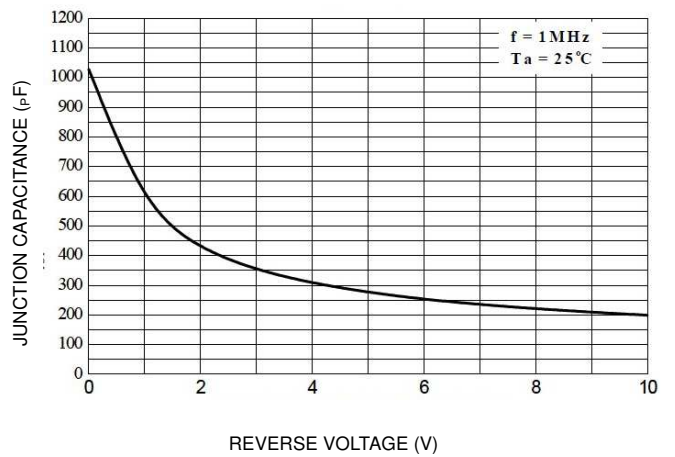
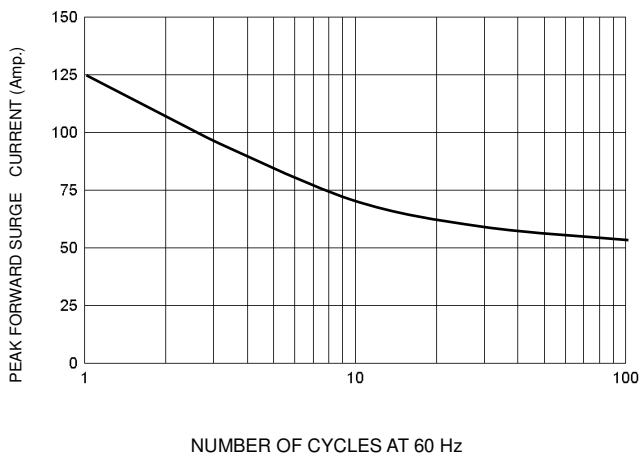


FIG-5 TYPICAL PEAK FORWARD SURGE CURRENT



## Notice

MOSPEC reserves the rights to make changes of the content herein the document anytime without notification. MOSPEC or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies. Please refer to MOSPEC website for the last document.

MOSPEC disclaims any and all liability arising out of the application or use of any product including damages incidentally and consequentially incurred.

Application shown on the herein document are examples of standard use and operation. Customers are responsible for comprehending suitable use in particular applications. MOSPEC makes no representation or warranty that such application will be suitable for the specified use without further testing or modification.

The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by MOSPEC for any infringements of patents or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of MOSPEC or others.

These MOSPEC products are intended for usage in general electronic equipment. Please make sure to consult with MOSPEC before you use these MOSPEC products in equipment which require specialized quality and/or reliability, and in equipment which could have major impact to the welfare of human life ( atomic energy control, aeronautics , traffic control, combustion control, safety devices etc.)